



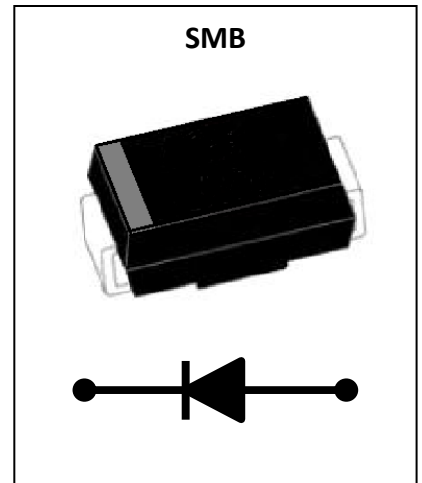
SS510L Schottky Barrier Diode

Feature

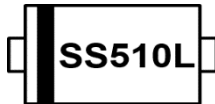
- Low VF
- High Junction Temperature
- High surge current capability

Applications

- Rectifier



MARKING:



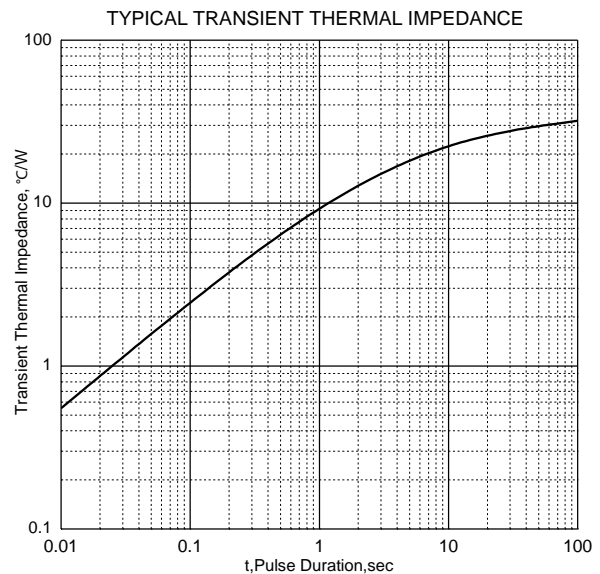
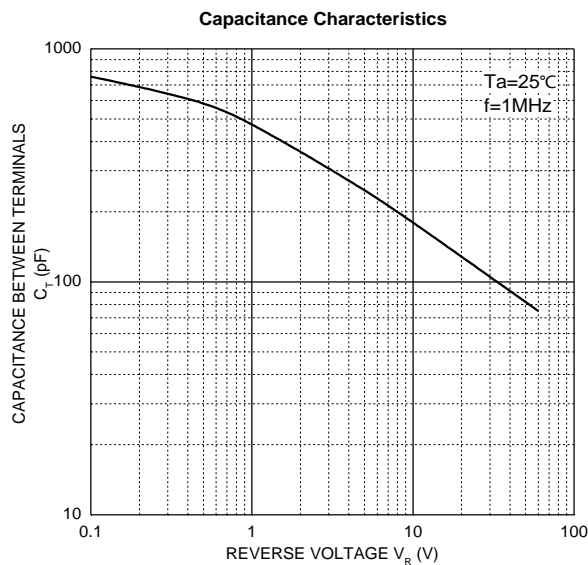
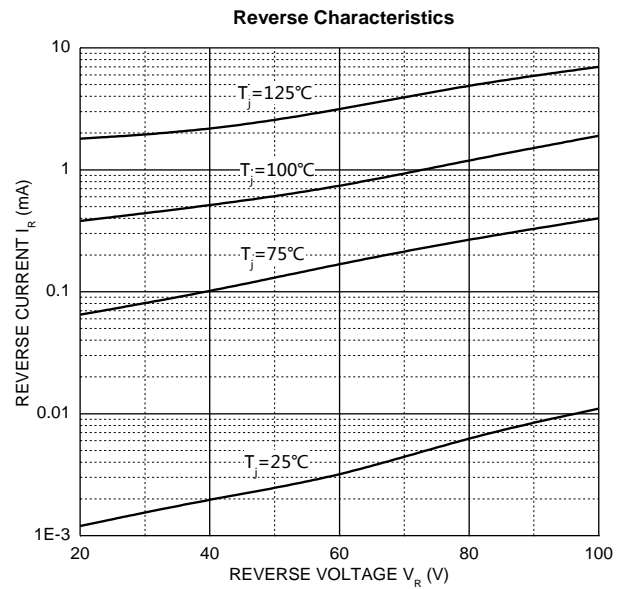
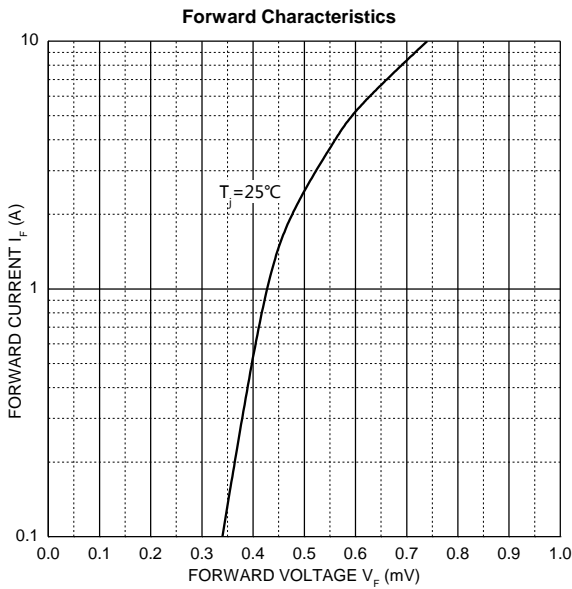
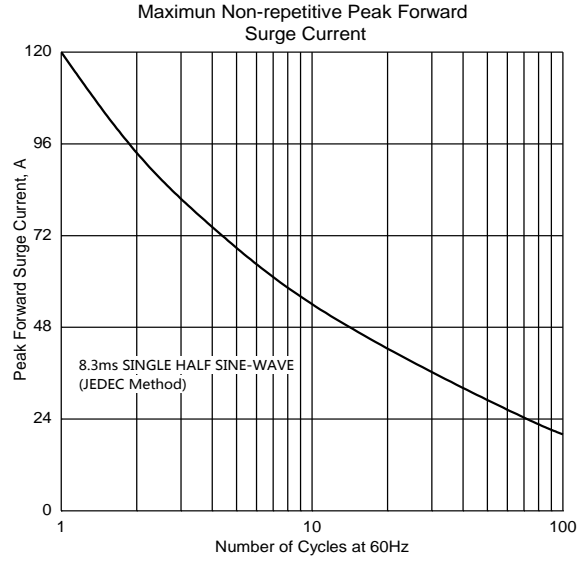
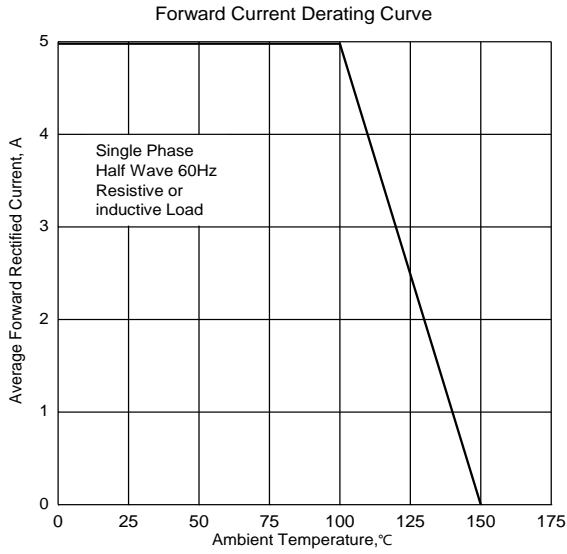
ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
DC reverse voltage	V_R	100	V
Mean rectifying current	I_o	5.0	A
Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	120	A
Power dissipation	P_D	2.5	W
Thermal resistance from junction to ambient	$R_{\theta JA}$	50	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

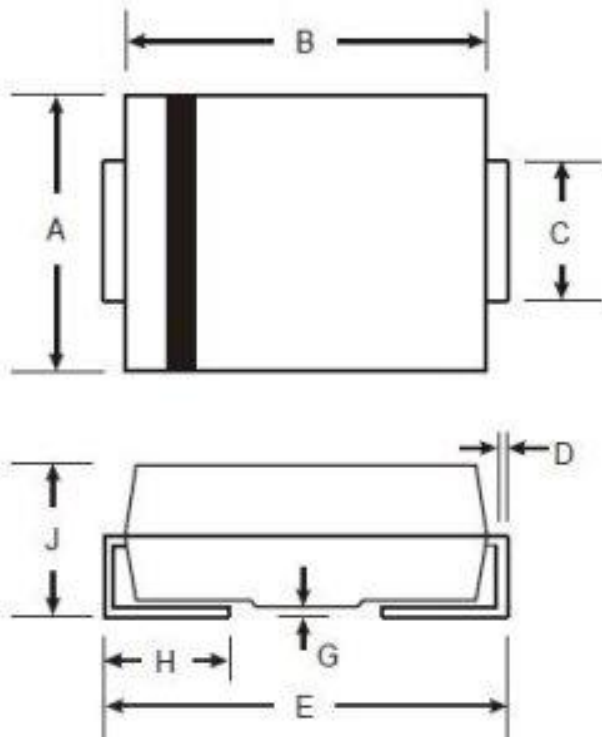
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V_{BR}	$I_R = 250\mu\text{A}$	100	110		V
Forward voltage	V_F	$I_F = 1\text{A}$	0	0.43	0.49	V
		$I_F = 3\text{A}$	0	0.52	0.58	V
		$I_F = 5\text{A}$	0	0.58	0.63	V
Reverse current	I_R	$V_R = 100\text{V}$		10	30	μA
		$V_R = 100\text{V}, T_a = 125^{\circ}\text{C}$			30	mA
Diode capacitance	C_D	$V_R = 4\text{V}, f = 1\text{MHz}$		200		pF

Typical Characteristics



SMB Package Outline Dimensions



SMA		
Dim	Min	Max
A	3.30	3.94
B	4.06	4.57
C	1.96	2.21
D	0.15	0.31
E	5.00	5.59
G	0.05	0.20
H	0.76	1.52
J	2.00	2.50
All Dimensions in mm		

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)